

#### **Features**

- Trench Power MV MOSFET Technology
- · Excellent Package for Heat Dissipation
- High Density Cell Design for Low R<sub>DS(on)</sub>
- Epoxy Meets UL 94 V-0 Flammability Rating
- Moisture Sensitivity Level 3
- Halogen Free. "Green" Device (Note 1)
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

# **Maximum Ratings**

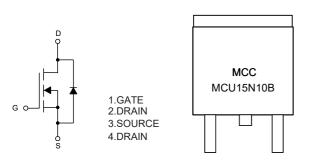
- Operating Junction Temperature Range: -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 3°C/W Junction to Case

Parameter	Symbol	Rating	Unit	
Drain-Source Voltage		V <sub>DS</sub>	100	V
Gate-Source Volltage		V <sub>GS</sub>	±20	V
Continuous Drain Current	T <sub>C</sub> =25°C	1_	15	Α
	T <sub>C</sub> =100°C	- I <sub>D</sub>	9.4	Α
Pulsed Drain Current	I <sub>DM</sub>	55	Α	
Single Pulse Avalanche Energy <sup>(Note 2)</sup>		E <sub>AS</sub>	4	mJ
Total Power Dissipation		P <sub>D</sub>	41	W

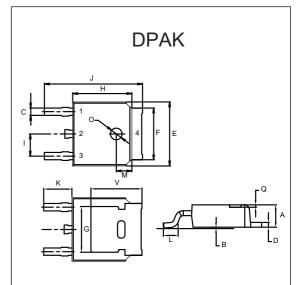
#### Note:

- 1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 2.EAS Condition: $T_J=25^{\circ}C, V_{DD}=25V, V_G=10V, R_q=25\Omega$ .

# **Internal Structure and Marking Code**



# N-CHANNEL MOSFET



DIMENSIONS					
DIM INCHES		HES	MM		NOTE
DIIVI	MIN	MAX	MIN	MAX	NOTE
Α	0.087	0.094	2.20	2.40	
В	0.000	0.005	0.00	0.13	
С	0.026	0.034	0.66	0.86	
D	0.018	0.023	0.46	0.58	
Е	0.256	0.264	6.50	6.70	
F	0.201	0.215	5.10	5.46	
G	0.190		4.83		TYP.
Н	0.236	0.244	6.00	6.20	
ı	0.086	0.094	2.18	2.39	
J	0.386	0.409	9.80	10.40	
K	0.114		2.90		TYP.
L	0.055	0.067	1.40	1.70	
М	0.063		1.60		TYP.
0	0.043	0.051	1.10	1.30	
Q	0.000	0.012	0.00	0.30	
V	0.211		5.35		TYP.



# Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Static Characteristics				1	1	I
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0V, I_D = 250 \mu A$	100			V
Gate-Source Leakage Current	I <sub>GSS</sub>	$V_{DS} = 0V, V_{GS} = \pm 20V$			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =100V, V <sub>GS</sub> =0V			1	μΑ
Gate-Threshold Voltage <sup>(Note 3)</sup>	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_D=250\mu A$	1.2		2.5	V
Drain-Source On-Resistance <sup>(Note 3)</sup>	В	V <sub>GS</sub> =10V, I <sub>D</sub> =5A		65	90	mO.
	$R_{DS(on)}$	V <sub>GS</sub> =4.5V, I <sub>D</sub> =3A		75	110	mΩ
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =15A			1.2	V
Continuous Body Diode Current	Is				15	Α
Dynamic Characteristics(Note 4)						
Input Capacitance	C <sub>iss</sub>			1100		pF
Output Capacitance	C <sub>oss</sub>	$V_{DS}$ =15V, $V_{GS}$ =0V,f=1MHz		55		
Reverse Transfer Capacitance	C <sub>rss</sub>			40		
Total Gate Charge	Qg			12		
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 50V, V_{GS} = 10V, I_{D} = 5A$		2.9		nC
Gate-Drain Charge	$Q_{gd}$			1.8		
Turn-On Delay Time	t <sub>d(on)</sub>			3.9		
Turn-On Rise Time	t <sub>r</sub>	V <sub>GS</sub> =10V,V <sub>DD</sub> =50V,I <sub>D</sub> =5A		26		10.0
Turn-Off Delay Time	t <sub>d(off)</sub>	$R_{GEN}$ =3 $\Omega$		16.2		- ns
Turn-Off Fall Time	t <sub>f</sub>			8.9		

Note 3. Pulse Test : Pulse Width≤300µs, Duty Cycle ≤2%.

<sup>4.</sup> Guaranteed by Design, Not Subject to Production Testing.



## **Curve Characteristics**

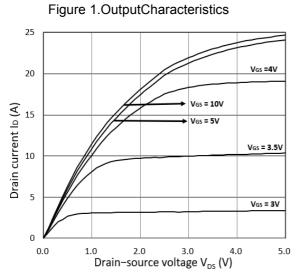


Figure 2. TransferCharacteristics

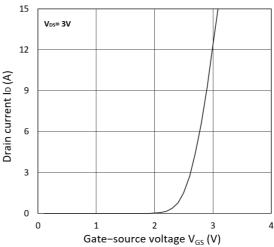


Figure 3.Forward CharacteristicsofReverse

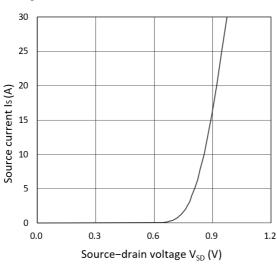


Figure 4. Gate Charge Characteristics

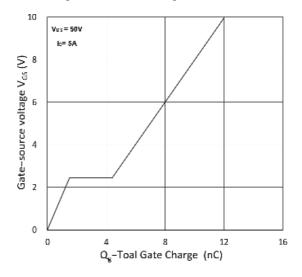


Figure 5.R<sub>DS(on)</sub>vs.V<sub>GS</sub>

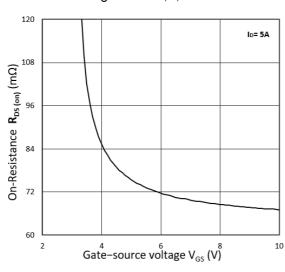
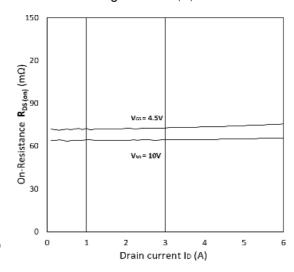


Figure 6.  $R_{DS(on)}$  vs. $I_D$ 





## **Curve Characteristics**

Figure 7.Capacitance Characteristics

Figure 8. Safe OperatingArea

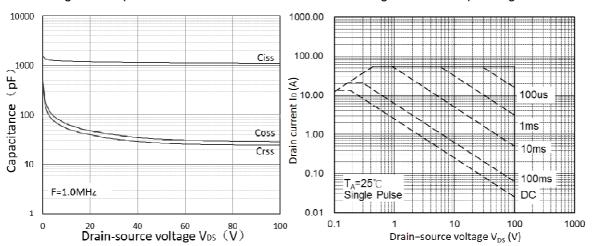
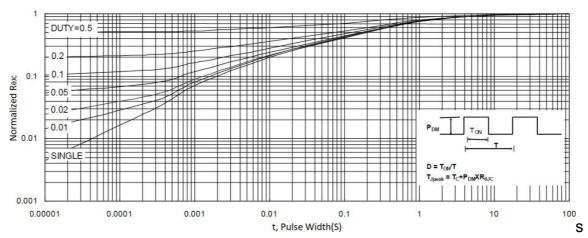


Figure 9.Normalized Maximum Transient Thermal Impedance



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# **Ordering Information**

Device	Packing	
Part Number-TP	Tape&Reel: 2.5Kpcs/Reel	

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